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Kind regards,

Team Nexperia

PMP5501V; PMP5501G; PMP5501Y

PNP/PNP matched double transistors

Rev. 03 — 28 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP matched double transistors in small Surface-Mounted Device (SMD) plastic packages. The transistors in the SOT666 and SOT363 (SC-88) packages are fully isolated internally.

Table 1. Product overview

Type number	pe number Package PNP/PNP h _{FE1} /h _{FE2}		NPN/NPN		
	NXP	JEITA	0.98 complement	complement	
PMP5501V	SOT666	-	PMP5201V	PMP4501V	
PMP5501G	SOT353	SC-88A	PMP5201G	PMP4501G	
PMP5501Y	SOT363	SC-88	PMP5201Y	PMP4501Y	

1.2 Features

- Current gain matching
- Base-emitter voltage matching
- Common emitter configuration for SOT353 types
- Application-optimized pinout

1.3 Applications

- Current mirror
- Differential amplifier

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
V _{CEO}	collector-emitter voltage	open base	-	-	-45	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	200	290	450	



Table 2. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
h _{FE1} /h _{FE2}	h _{FE} matching	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	[1] 0.95	1	-	
V _{BE1} -V _{BE2}	V _{BE} matching	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	[2] _	-	2	mV

^[1] The smaller of the two values is taken as the numerator.

2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
SOT666;	SOT363		
1	base TR1		
2	base TR2	6 5 4	6 5 4
3	collector TR2		TR1 TR2
4	emitter TR2		
5	emitter TR1		1 2 3 006aaa550
6	collector TR1	001aab555	000aaa330
SOT353			
1	base TR1	Π- Π.	_
2	emitter TR1, TR2	5 4	5 4
3	base TR2		TR1 TR2
4	collector TR2		
5	collector TR1	<u> </u>	1 2 3 006aaa551

3. Ordering information

Table 4. Ordering information

Type number	Package						
	Name	Description	Version				
PMP5501V	-	plastic surface-mounted package; 6 leads	SOT666				
PMP5501G	SC-88A	plastic surface-mounted package; 5 leads	SOT353				
PMP5501Y	SC-88	plastic surface-mounted package; 6 leads	SOT363				

^[2] The smaller of the two values is subtracted from the larger value.

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PMP5501V	ED
PMP5501G	R4*
PMP5501Y	S6*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-45	V
V_{EBO}	emitter-base voltage	open collector	-	- 5	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT666		[1][2]	200	mW
	SOT353		<u>[1]</u> _	200	mW
	SOT363		<u>[1]</u> _	200	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT666		[1][2]	300	mW
	SOT353		<u>[1]</u> _	300	mW
	SOT363		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

^[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2] _	-	625	K/W
	SOT353		[1] -	-	625	K/W
	SOT363		[1] -	-	625	K/W
Per device	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2]	-	416	K/W
	SOT353		<u>[1]</u> -	-	416	K/W
	SOT363		<u>[1]</u> -	-	416	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Per transistor								
I_{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V};$ $I_E = 0 \text{ A}$	-	-	–15	nA		
		$V_{CB} = -30 \text{ V};$ $I_{E} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	- 5	μΑ		
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V};$ $I_C = 0 \text{ A}$	-	-	-100	nA		
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \mu\text{A}$	-	250	-			
		$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	200	290	450			
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	-	-50	-200	mV		
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	-	-200	-400	mV		
V_{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	[1] -	-760	-	mV		
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	[1] _	-920	-	mV		

^[2] Reflow soldering is the only recommended soldering method.

Table 8. Characteristics ...continued $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

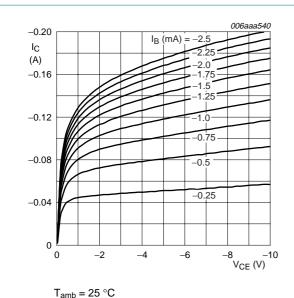
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{BE}	base-emitter voltage	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	<u>[2]</u> –600	-650	-700	mV
		$V_{CE} = -5 \text{ V};$ $I_C = -10 \text{ mA}$	[2] -	-	-760	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	2.2	pF
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	10	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$	100	175	-	MHz
NF	noise figure	$V_{CE} = -5 \text{ V};$ $I_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 10 \text{ Hz to}$ 15.7 kHz	-	1.6	-	dB
		$V_{CE} = -5 \text{ V};$ $I_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 1 \text{ kHz};$ $B = 200 \text{ Hz}$	-	3.1	-	dB
Per device						
h _{FE1} /h _{FE2}	h _{FE} matching	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	[3] 0.95	1	-	
$V_{BE1}-V_{BE2}$	V _{BE} matching	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	<u>[4]</u> _	-	2	mV

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

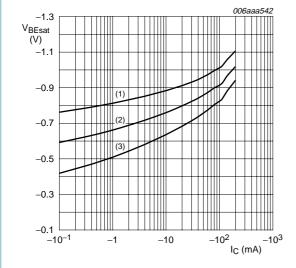
^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] The smaller of the two values is taken as the numerator.

^[4] The smaller of the two values is subtracted from the larger value.



Collector current as a function of Fig 1. collector-emitter voltage; typical values



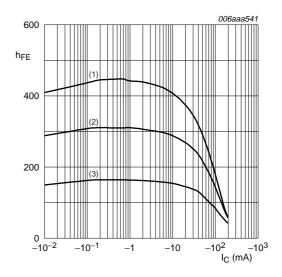
 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = -55 \,^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 3. Base-emitter saturation voltage as a function of collector current; typical values



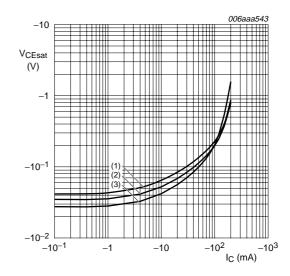
 $V_{CE} = -5 \text{ V}$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55$ °C

DC current gain as a function of collector Fig 2. current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Collector-emitter saturation voltage as a Fig 4. function of collector current; typical values

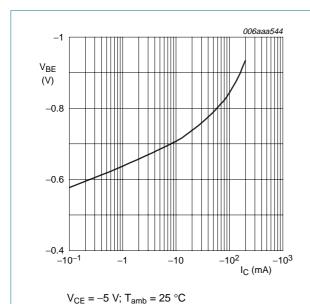


Fig 5. Base-emitter voltage as a function of collector current; typical values

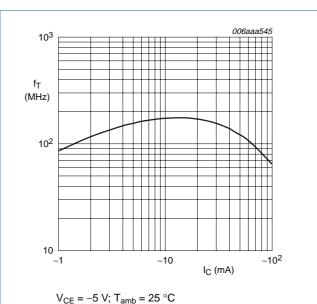


Fig 6. Transition frequency as a function of collector current; typical values

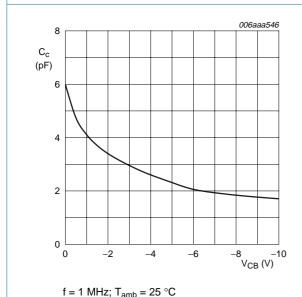


Fig 7. Collector capacitance as a function of collector-base voltage; typical values

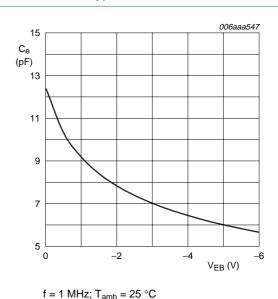
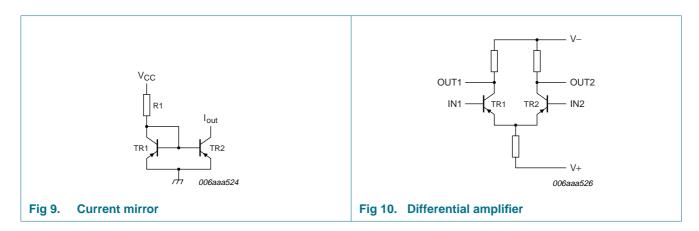
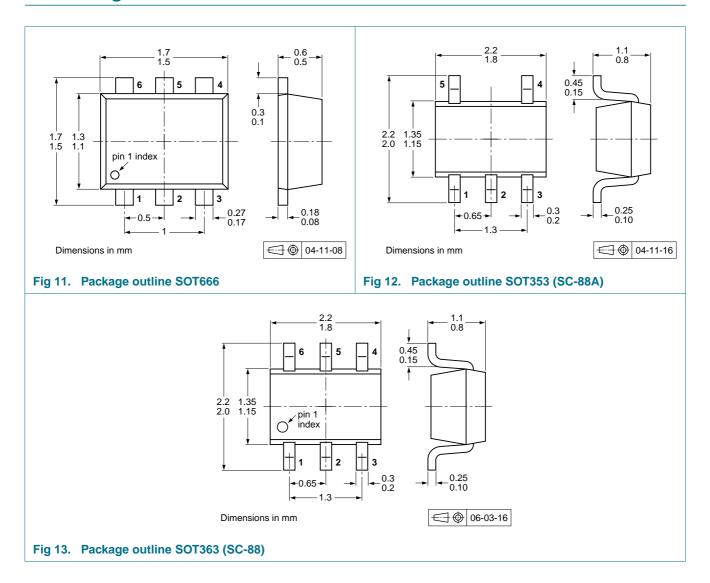


Fig 8. Emitter capacitance as a function of emitter-base voltage; typical values

8. Application information



9. Package outline



10. Packing information

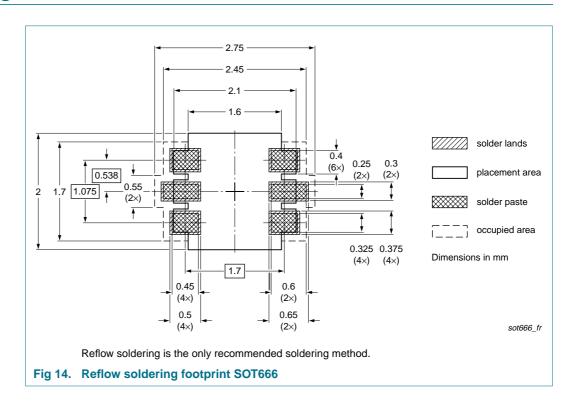
Table 9. Packing methods

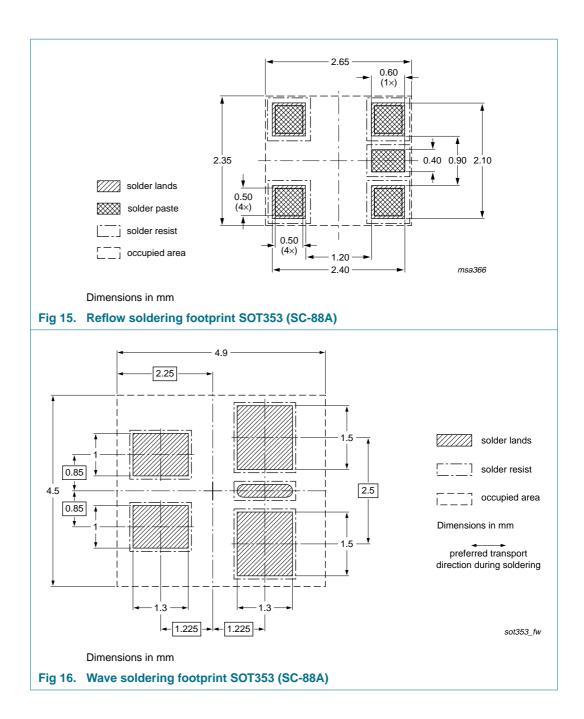
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

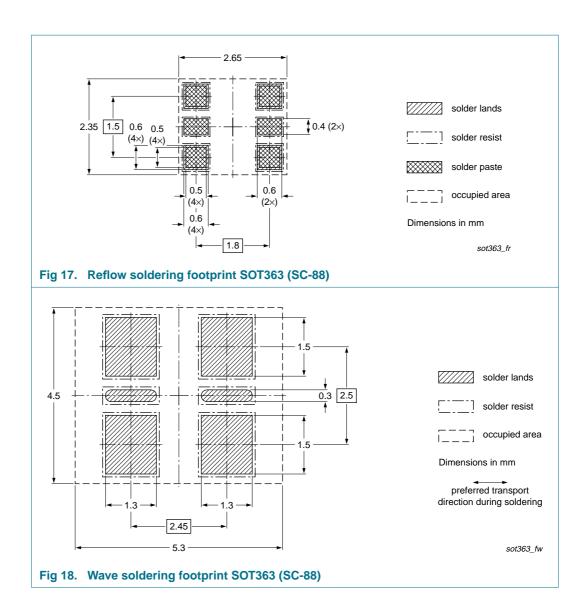
Type number	Package	Description		Packing quantity			
				3000	4000	8000	10000
PMP5501V SOT666		2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PMP5501G	SOT353	4 mm pitch, 8 mm tape and reel		-115	-	-	-135
PMP5501Y	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PMP5501V_G_Y_3	20090828	Product data sheet	-	PMP5501V_G_Y_2			
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 						
	Figure 14 "R	eflow soldering footprint SOT	666": updated				
	Figure 16 "W	lave soldering footprint SOT3	53 (SC-88A)": update	ed			
	• Figure 17 "R	eflow soldering footprint SOT	363 (SC-88)": update	d			
	Figure 18 "W	lave soldering footprint SOT3	63 (SC-88)": updated				
PMP5501V_G_Y_2	20060919	Product data sheet	-	PMP5501G_Y_1			
PMP5501G_Y_1	20060221	Product data sheet	-	-			

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PMP5501V; PMP5501G; PMP5501Y

NXP Semiconductors

PNP/PNP matched double transistors

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